

Supporting Information for: High-throughput Screening and Classification of Layered Di-Metal Chalcogenides

Table S1. The setup for generating the Monkhorst-Pack k-point meshes of 24 listed LDCs in Table 2.

| Compounds | Number of k points | | | Compounds | Number of k points | | |
|---|--------------------|----------------|----------------|---|--------------------|----------------|----------------|
| | b ₁ | b ₂ | b ₃ | | b ₁ | b ₂ | b ₃ |
| 1 CsAg ₃ Se ₂ | 8 | 8 | 4 | 13 Cu ₃ TlSe ₂ | 8 | 4 | 4 |
| 2 KAgSe | 8 | 8 | 4 | 14 Cs ₃ Bi ₇ Se ₁₂ | 4 | 4 | 4 |
| 3 KCuSe | 8 | 8 | 4 | 15 BaCu ₂ S ₂ | 8 | 8 | 6 |
| 4 Rb ₂ Ag ₄ S ₃ | 8 | 8 | 8 | 16 BaCu ₂ Se ₂ | 8 | 8 | 6 |
| 5 CsAg ₃ S ₂ | 8 | 4 | 4 | 17 MgAl ₂ S ₄ | 6 | 6 | 6 |
| 6 KCu ₃ S ₂ | 8 | 4 | 4 | 18 ZnIn ₂ S ₄ | 7 | 3 | 3 |
| 7 RbCu ₃ S ₂ | 8 | 8 | 8 | 19 Ba ₃ Zr ₂ S ₇ | 8 | 8 | 4 |
| 8 KAg ₃ Se ₂ | 8 | 4 | 4 | 20 Ba ₂ ZrS ₄ | 8 | 8 | 4 |
| 9 RbAg ₃ Se ₂ | 8 | 4 | 4 | 21 Ba ₄ Zr ₃ S ₁₀ | 6 | 6 | 6 |
| 10 K ₂ Ag ₄ Se ₃ | 8 | 8 | 8 | 22 TlInS ₂ | 10 | 10 | 2 |
| 11 RbNaS | 8 | 8 | 6 | 23 Bi ₂ PbSe ₄ | 5 | 5 | 5 |
| 12 Cu ₃ TlS ₂ | 8 | 8 | 8 | 24 Bi ₂ Pb ₂ Se ₅ | 8 | 8 | 2 |

Table S2. The in-plane direction which has the smallest effective mass and the corresponding effective mass of the LDCs in Fig. 6. As a result of the small effective mass, the carrier mobility along that in-plane direction may be high.

| Compounds | Carrier Type | k path | Effective mass (m_0) |
|--|--------------|------------------|--------------------------|
| BaCu ₂ S ₂ | electron | Γ -X | 0.20 |
| Ba ₂ ZrS ₄ | electron | Γ -X | 0.20 |
| KAgSe | electron | Γ -X | 0.17 |
| Cs ₃ Bi ₇ Se | electron | Y-X ₁ | 0.22 |
| | hole | Y-X ₁ | 0.26 |
| Rb ₂ Ag ₄ S ₃ | electron | Γ -N | 0.15 |
| | hole | Γ -X | 0.16 |
| TlInS ₂ | electron | K-M | 0.31 |
| | hole | Γ -A | 0.16 |
| Bi ₂ PbSe ₄ -bulk | electron | Z-P ₁ | 0.12 |
| | hole | Z-P ₁ | 0.24 |
| MgAl ₂ S ₄ -bulk | electron | Γ -X | 0.24 |
| | hole | Γ -L | 0.36 |
| ZnIn ₂ S ₄ -bulk | electron | Γ -Y | 0.21 |
| | hole | Γ -Y | 0.21 |
| Bi ₂ PbSe ₄ -monolayer | electron | Γ -M | 0.22 |
| | hole | Γ -M | 0.62 |
| MgAl ₂ S ₄ - monolayer | electron | Γ -K | 0.24 |
| | hole | Γ -K | 0.40 |
| ZnIn ₂ S ₄ - monolayer | electron | Γ -K | 0.24 |
| | hole | Γ -K | 0.34 |